(Tc = 25°C unless otherwise specified)

V_{DS}

(Tc = 25°C unless otherwise specified)

$V_{(BR)DSS}$	Drain-source breakdown voltage	750	-	-	V	V_{GS} = 0V, I_D = 100μA	
$V_{GS(th)}$	Gate threshold voltage	2.3	3.0	3.8	V	V_{DS} = V_{GS}, I_D = 4.5mA	Fig.11
		-	2.4	-	V	V_{DS} = V_{GS}, I_D = 4.5mA T_J = 175°C	
I_{DSS}	Zero gate voltage drain current	-	1	10	μA	V_{DS} = 750V, V_{GS} = 0V	
I_{GSS}	Gate source leakage current	-	-	100	nA	V_{GS} = 18V, V_{DS} = 0V	
$R_{DS(on)}$	Current drain-source on-state resista |						

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Q_{gs}	Gate source charge	-	8.5	-	nC	V_{DS} = 500V, V_{GS} = -4/+18V I_D = 14A	Fig.12
Q_{gd}	Gate drain charge	-	8	-			
Q_g	Gate charge	-	24	-			

(Tc = 25°C unless otherwise specified)

Figure 1. Output characteristics T_J = -55 ºC

Figure 2. Output characteristics T_J = 25 ºC

Figure 3. Output characteristics T_J = 175 ºC

Figure 4. Normalized o i

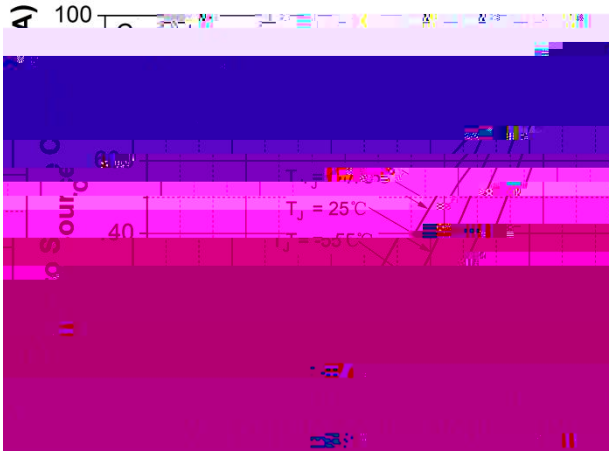


Figure 7. Transfer characteristic for various junction temperatures

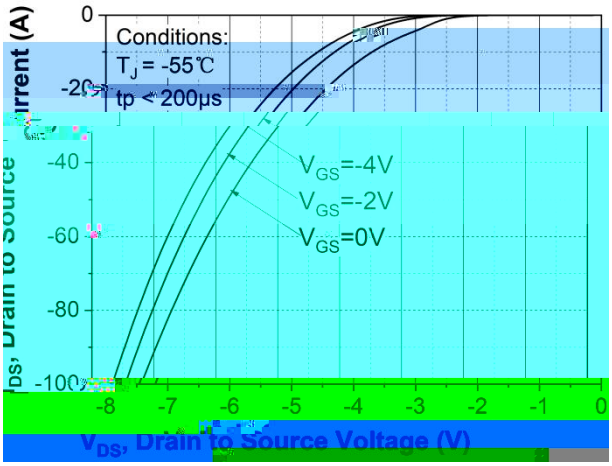


Figure 8. Body diode characteristic at T_J = -55 ºC

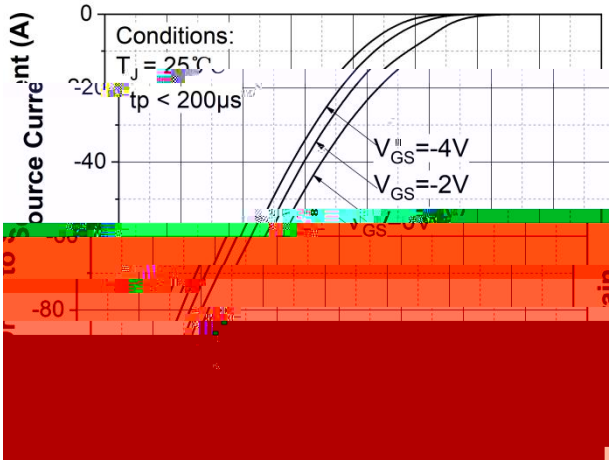


Figure 9. Body diode characteristic at T_J = 25 ºC

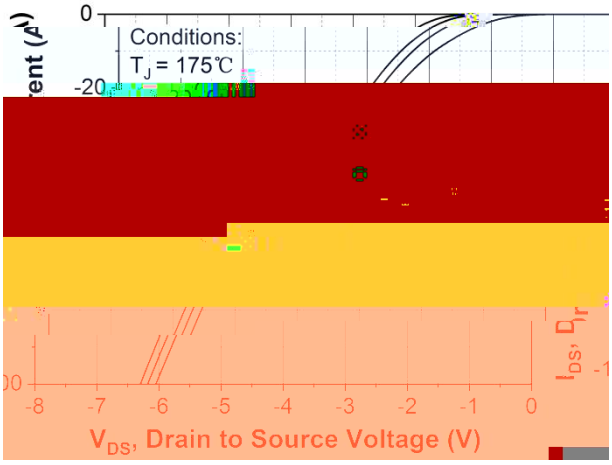


Figure 10. Body diode characteristic at T_J = 175ºC

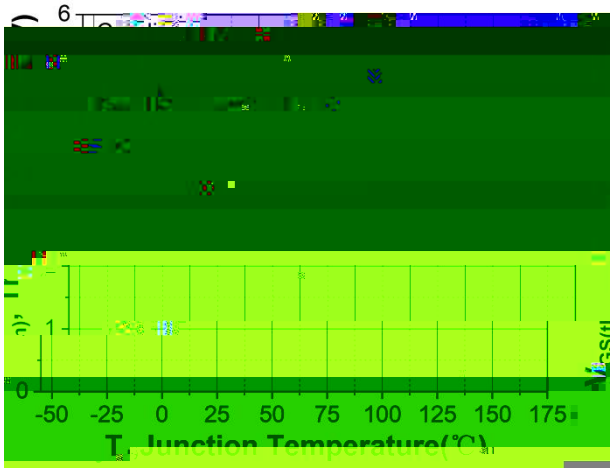


Figure 11. Threshold voltage vs. temperature

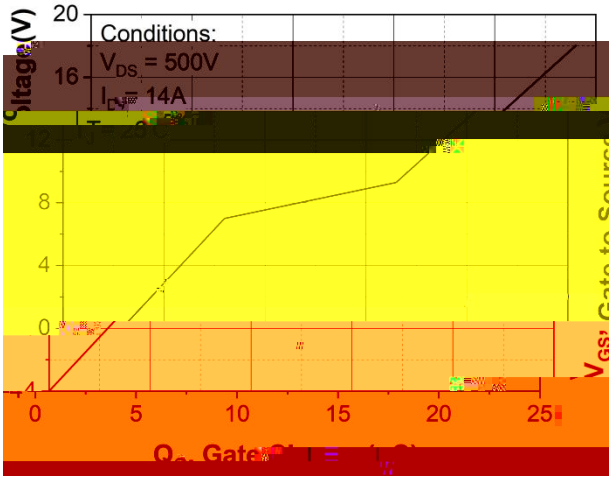


Figure 12. Gate charge characteristic

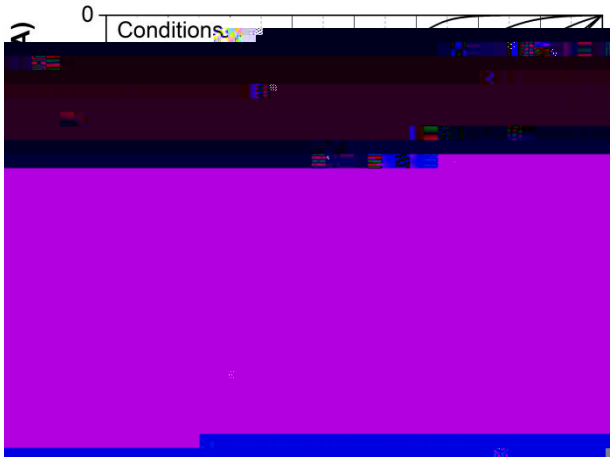


Figure 13. 3rd quadrant characteristic at T_J = -55 ºC

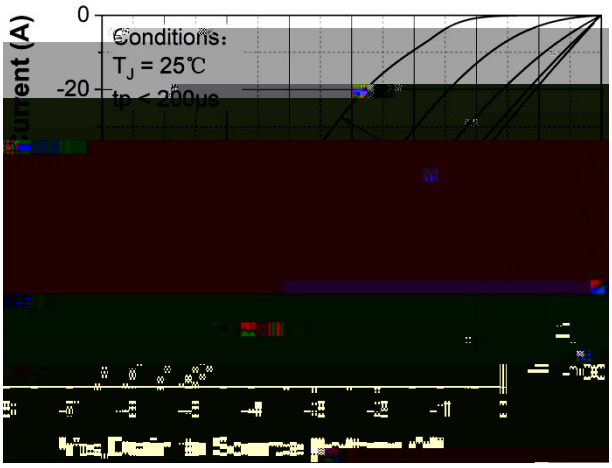


Figure 14. 3rd quadrant characteristic at T_J = 25 ºC

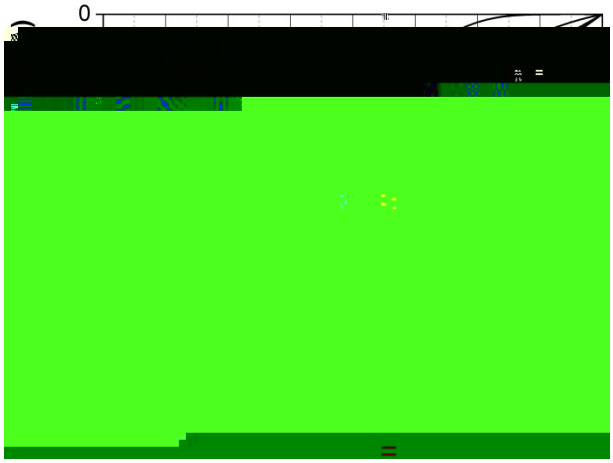


Figure 15. 3rd quadrant characteristic at T_J = 175 ºC

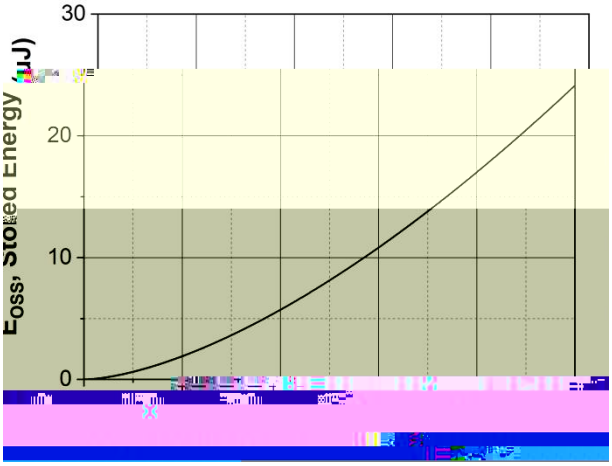


Figure 16. Output capacitor stored energy

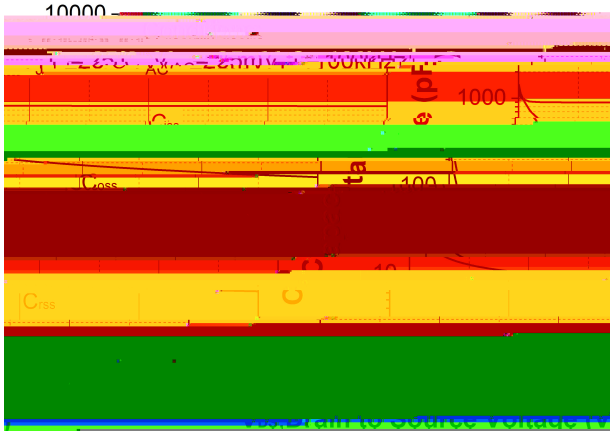


Figure 17. Capacitances vs. drain-source voltage (0 - 200V)

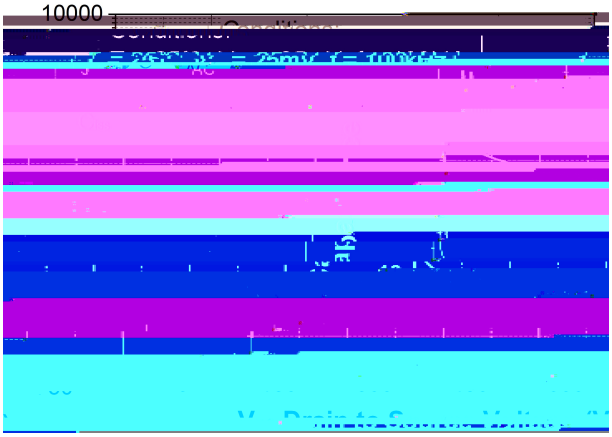


Figure 18. Capacitances vs. drain-source voltage (0 - 750V)

Figure 19. Continuous drain current derating vs. case temperature

Figure 20. Maximum powe

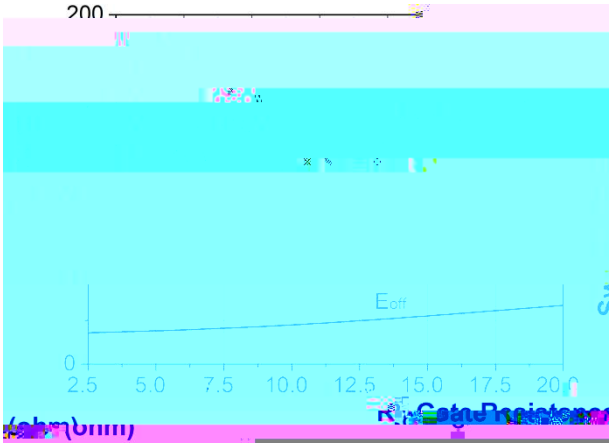


Figure 25. Clamped inductive switching energy vs. R_G (ext)

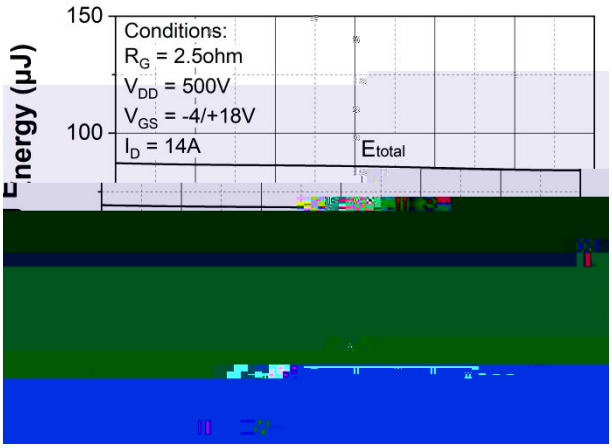


Figure 26. Clamped inductive switching energy vs. temperature

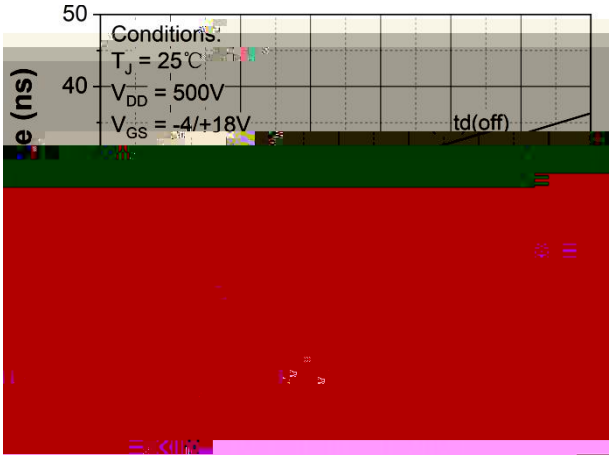
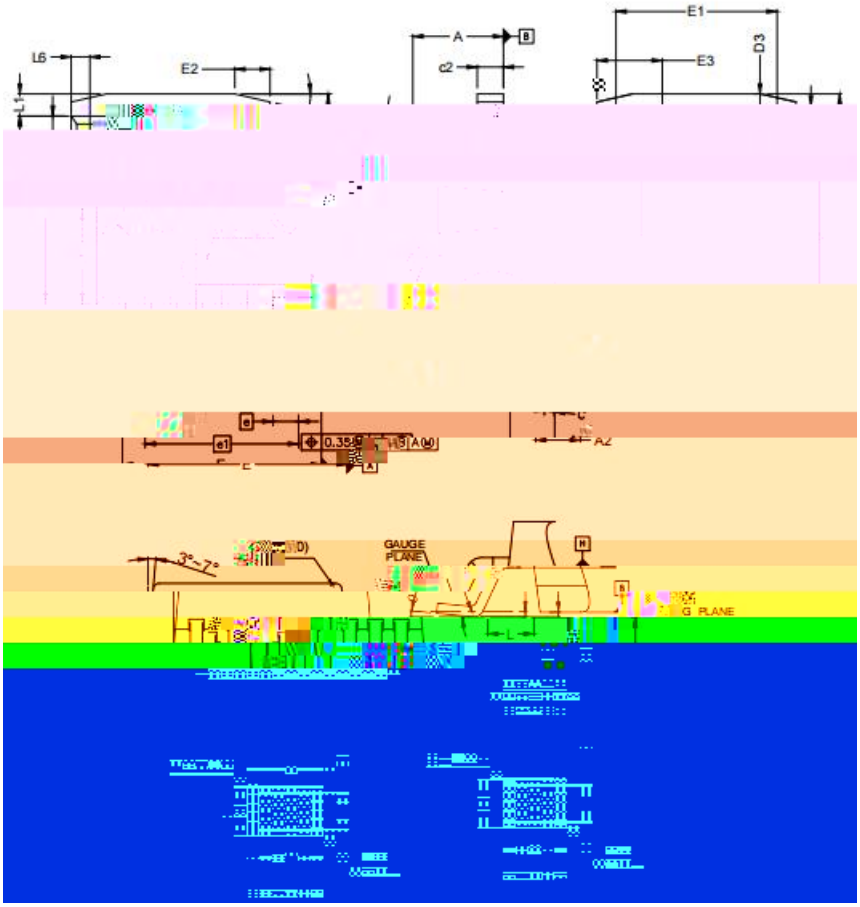
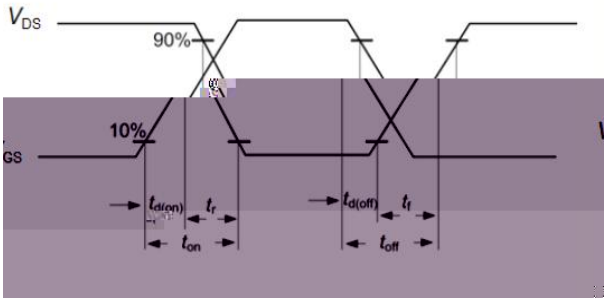


Figure 27. Switching times vs. R_G (ext)

(TO-263-7L-A)



SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	4.30				



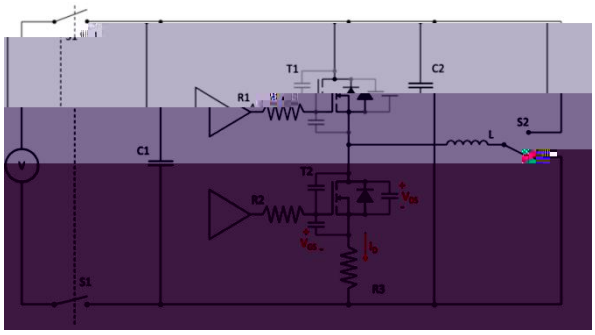


Figure A. Definition of switchjfĎ ή D

7. Except as otherwise explicitly approved by Sichain in a written document signed by authorized representatives of Sichain, Sichain' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

8. For use of our products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a Sichain representatives, for example but not limited to: transportation equipment,primary communication equipment,traffic lights,fire/crime prevention, safety equipment, medical systems, and power transmission systems.